# Hyper Fast Rectifier, 2 x 3 A FRED Pt®



PRODUCT SUMMARY							
Package	FlatPAK 5 x 6						
I <sub>F(AV)</sub>	2 x 3 A						
$V_{R}$	200 V						
V <sub>F</sub> at I <sub>F</sub>	0.71 V						
+	25 ne						

175 °C

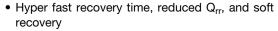
Separated cathode

T<sub>.I</sub> max.

Diode variation

3.4 • • 5,6

#### **FEATURES**





HALOGEN

**FREE** 

- 175 °C maximum operating junction temperature
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

M3 suffix meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		$V_{RRM}$		200				
Average rectified forward current	per device	I <sub>F(AV)</sub>	T <sub>Solderpad</sub> = 170 °C, DC	3	V			
Average rectilled forward current	per device		T <sub>Solderpad</sub> = 169 °C, D = 0.5	3				
Non-repetitive peak surge current	per device	1	T <sub>J</sub> = 25 °C, 10 ms sinusoidal pulse	147	Α			
	per diode	IFSM		70	A			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. U								
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 3 A	-	0.88	0.94	V		
		I <sub>F</sub> = 3 A, T <sub>J</sub> = 150 °C	-	0.71	0.74			
Reverse leakage current	I <sub>R</sub>	$V_R = V_R$ rated	-	-	2	μA		
neverse leakage current		$T_J = 150  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	6	40	μΑ		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	14	-	pF		



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt = 50$	$0 \text{ A/}\mu\text{s}, V_{\text{R}} = 30 \text{ V}$	-	26	-		
	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	25		
		T <sub>J</sub> = 25 °C		-	15	-	ns	
		T <sub>J</sub> = 125 °C	$I_F = 3 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	25	-		
Dools recovery assured	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2	-	۸	
Peak recovery current				-	3	-	А	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	12	-	200	
		T <sub>J</sub> = 125 °C		-	40	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C			
Thermal resistance, junction to ambient	R <sub>thJA</sub> (1)(2)		-	90	103				
Thermal resistance, junction to case	R <sub>thJC</sub> <sup>(3)</sup>		-	2.3	2.6	°C/W			

#### **Notes**

- $^{(1)}$  The heat generated must be less than thermal conductivity from junction to ambient;  $dP_D/dT_J < 1 \times R_{thJA}$
- (2) Free air, mounted or recommended copper pad area; thermal resistance R<sub>thJA</sub> junction to ambient
- (3) Mounted on infinite heatsink

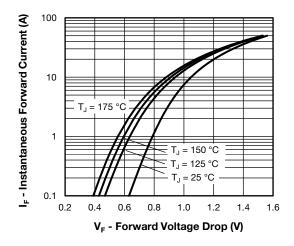


Fig. 1 - Typical Forward Voltage Drop Characteristics

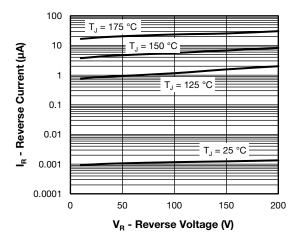


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



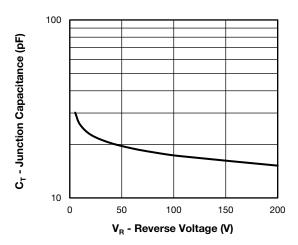


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

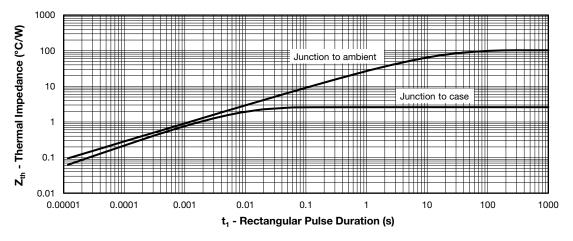


Fig. 4 - Maximum Thermal Impedance Z<sub>th</sub> Characteristics

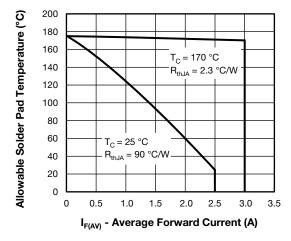


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

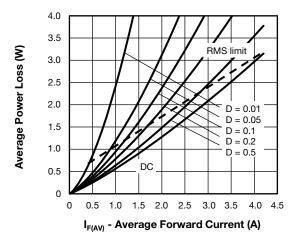


Fig. 6 - Forward Power Loss Characteristics

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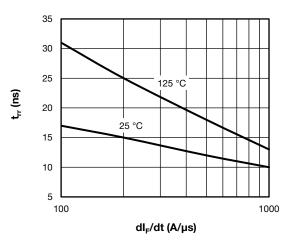


Fig. 7 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

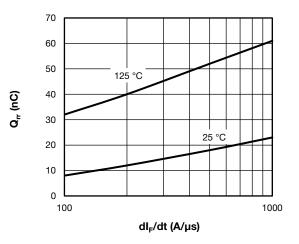
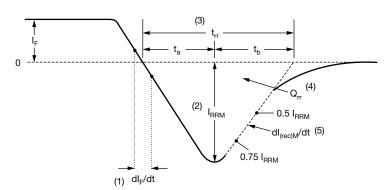


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see Fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

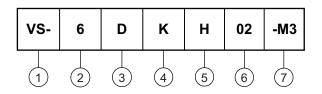
(5)  $dl_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 9 - Reverse Recovery Waveform and Definitions



### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (6 = 6 A)

Circuit configuration:

D = separated cathode

4 - K = FlatPAK package

5 - Process type:

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

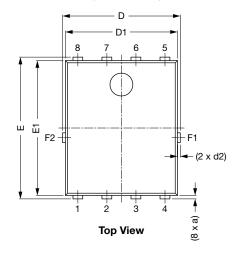
7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

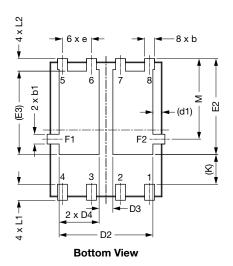
ORDERING INFORMATION (Example)								
PREFERRED P/N	D P/N UNIT WEIGHT (g) PREFERRED PACKAGE CODE BASE QUANTITY PACKAGING DESCRIPTION							
VS-6DKH02-M3/H	0.10	Н	1500	7"diameter plastic tape and reel				
VS-6DKH02-M3/I	0.10	I	6000	13"diameter plastic tape and reel				

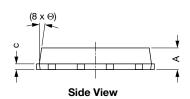
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96056					
Part marking information	www.vishay.com/doc?96059					
Packaging information	www.vishay.com/doc?88869					

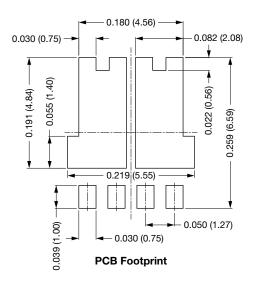
# FlatPAK 5 x 6 (Dual)

### **DIMENSIONS** in inches (millimeters)









DIM		INCHES		MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.035	0.039	0.043	0.89	0.99	1.09	
(a)	-	0.006	-	-	0.15	-	
b	0.013	0.017	0.020	0.32	0.43	0.52	
b1	0.013	0.017	0.020	0.32	0.43	0.52	
С	0.008	-	0.014	0.20	-	0.35	
D	0.197	0.203	0.209	5.00	5.15	5.30	
D1	0.189	0.193	0.197	4.80	4.90	5.00	
D2	0.154	0.161	0.169	3.90	4.10	4.30	
D3	0.020	0.024	0.031	0.50	0.60	0.80	
D4	0.063	0.069	0.075	1.60	1.75	1.90	
(d1)	-	0.016	-	=	0.40	=	
(d2)	-	0.005	-	-	0.125	-	
Е	0.238	0.244	0.250	6.05	6.20	6.35	



## **Outline Dimensions**

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DIM.		INCHES			MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
E1	0.228	0.232	0.236	5.80	5.90	6.00		
E2	0.157	0.165	0.173	4.00	4.20	4.40		
(E3)	-	0.144	=	-	3.65	=		
е		0.050 BSC			1.27 BSC			
(K)	0.039	-	-	1.00	-	-		
L1	0.019	-	0.043	0.48	-	1.10		
L2	0.012	-	0.031	0.30	-	0.80		
M	0.128	0.138	0.148	3.25	3.50	3.75		
Θ	0°	-	10°	0°	-	10°		

#### Notes

- Dimensioning and tolerancing per ASME Y14.5-2009
- Dimensions D1 and E1 do not include mold flash or gate burrs
- Dimension (XX) means reference only



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